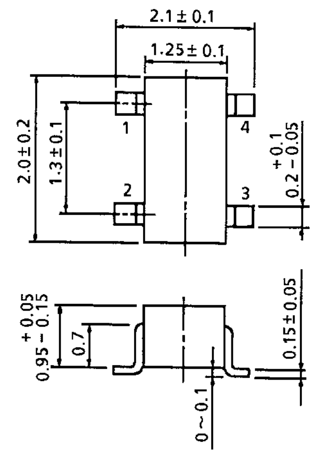
TOSHIBA Diode Silicon Epitaxial Planar Type

1SS382

Ultra High Speed Switching Application

Unit: mm



1. ANODE 1
2. ANODE 2
3. CATHODE 2
4. CATHODE 1

USQ

JEDEC	―
EIAJ	―
TOSHIBA	1-2U1A

Weight: 0.006g

- Small package
- Composed of 2 independent diodes.
- Low forward voltage : $V_{F\ (3)} = 0.92V$ (typ.)
- Fast reverse recovery time: $T_{rr} = 1.6ns$ (typ.)

Maximum Ratings (Ta = 25°C)

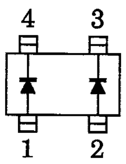
Characteristic	Symbol	Rating	Unit
Maximum (peak) reverse Voltage	V_{RM}	85	V
Reverse voltage	V_R	80	V
Maximum (peak) forward current	I_{FM}	300 *	mA
Average forward current	I_O	100 *	mA
Surge current (10ms)	I_{FSM}	2	A
Power dissipation	P	100 *	mW
Junction temperature	T_j	125	°C
Storage temperature range	T_{stg}	−55~125	°C

*: Unit rating. Total rating = unit rating × 1.5

Electrical Characteristics (Ta = 25°C)

Characteristic	Symbol	Test Circuit	Test Condition	Min	Typ.	Max	Unit
Forward voltage	$V_{F\ (1)}$	―	I_F = 1mA	―	0.61	―	V
	$V_{F\ (2)}$	―	I_F = 10mA	―	0.74	―	V
	$V_{F\ (3)}$	―	I_F = 100mA	―	0.92	1.20	V
Reverse current	$I_{R\ (1)}$	―	V_R = 30V	―	―	0.1	μA
	$I_{R\ (2)}$	―	V_R = 80V	―	―	0.5	μA
Total capacitance	CT	―	VR = 0, f = 1MHz	―	0.9	2.0	pF
Reverse recovery time	trr	―	IF = 10mA, Fig.1	―	1.6	4.0	ns

Pin Assignment (Top View)



Marking